



TELECOM EQUIPMENT PROTECTION: TRISIL™

PRELIMINARY DATASHEET

FEATURES

- Bidirectional crowbar protection
- Voltage range from 65V to 270V
- Low V_{BO} / V_R ratio
- Micro capacitance from 20 to 30pF typ @ 50V
- Low leakage current : $I_R = 2 \mu A$ max
- Holding current: $I_H = 150$ mA min
- Repetitive peak pulse current :
 $I_{PP} = 100$ A (10/1000 μs)

MAIN APPLICATIONS

Any sensitive equipment requiring protection against lightning strikes and power crossing:

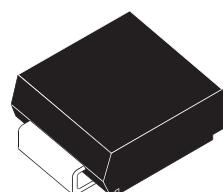
- Analog and digital line cards (ADSL, VDSL, T1/ E1, ISDN...)
- Terminals (phone, fax, modem...) and central of-office equipment

DESCRIPTION

The SMP100MC-xxx series is a micro capacitance transient surge arrestor designed for the protection of high debit rate communication equipment. Its micro capacitance avoids any distortion of the signal and is compatible with digital line cards (ADSL, VDSL, T1/E1, ISDN...).

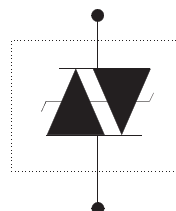
BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. They are used to help equipment to meet main standards such as UL1950, IEC950 / CSA C22.2 and UL1459. They have UL94 V0 approved resin. SMB package is JEDEC registered (DO-214AA). Trisils are UL497B approved (file: E136224) and comply with the following standards GR-1089 Core, ITU-T-K20/K21, VDE0433, VDE0878, IEC61000-4-5 and FCC part 68.



SMB
(JEDEC DO-214AA)

SCHEMATIC DIAGRAM



IN COMPLIANCES WITH THE FOLLOWING STANDARDS

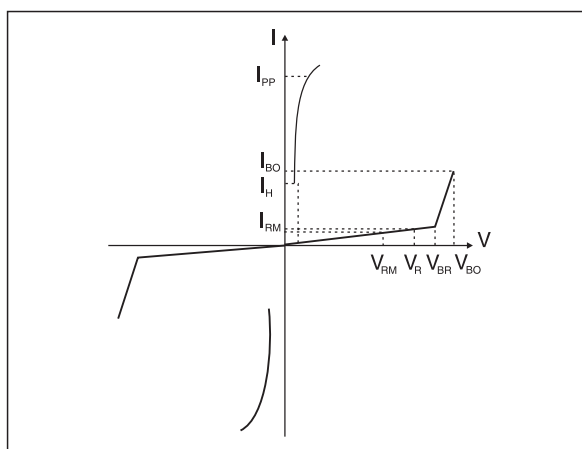
STANDARD	Peak Surge Voltage (V)	Voltage Waveform	Required peak current (A)	Current waveform	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500 1000	2/10 μ s 10/1000 μ s	500 100	2/10 μ s 10/1000 μ s	0 0
GR-1089 Core Second level	5000	2/10 μ s	500	2/10 μ s	0
GR-1089 Core Intra-building	1500	2/10 μ s	100	2/10 μ s	0
ITU-T-K20/K21	6000 1500	10/700 μ s	150 37.5	5/310 μ s	0 0
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000 2000	10/700 μ s	100 50	5/310 μ s	0 0
VDE0878	4000 2000	1.2/50 μ s	100 50	1/20 μ s	0 0
IEC61000-4-5	4000 4000	10/700 μ s 1.2/50 μ s	100 100	5/310 μ s 8/20 μ s	0 0
FCC Part 68, lightning surge type A	1500 800	10/160 μ s 10/560 μ s	200 100	10/160 μ s 10/560 μ s	0 0
FCC Part 68, lightning surge type B	1000	9/720 μ s	25	5/320 μ s	0

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient with recommended footprint	100	$^{\circ}\text{C/W}$
$R_{th(j-l)}$	Junction to leads	20	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$)

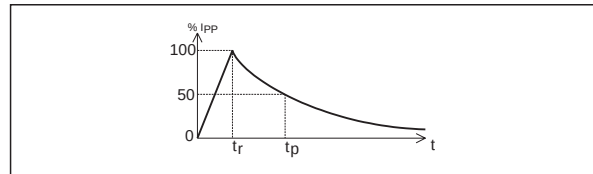
Symbol	Parameter
V_{RM}	Stand-off voltage
I_{RM}	Leakage current at V_{RM}
V_R	Continuous reverse voltage
I_R	Leakage current at V_R
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_H	Holding current
I_{BO}	Breakover current
I_{PP}	Peak pulse current
C	Capacitance



ABSOLUTE RATINGS ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter		Value	Unit
I_{pp}	Repetitive peak pulse current:		10/1000 μs	A
			8/20 μs	
			10/560 μs	
			5/310 μs	
			10/160 μs	
			1/20 μs	
			2/10 μs	
			500	
I_{FS}	Fail-safe mode : maximum current (note 1)	8/20 μs	5	kA
I_{TSM}	Non repetitive surge peak on-state current (Sinusoidal)		t = 20ms	TBD
			t = 16.6ms	50
			t = 0.2s	TBD
			t = 2s	TBD
I^2t	I^2t value for fusing	t = 16.6ms t = 20ms	TBD	A ² s
T_L	Maximum lead temperature for soldering during 10s		260	$^{\circ}\text{C}$
T_{stg} T_j	Storage temperature range		- 55 to + 150	$^{\circ}\text{C}$
	Maximum junction temperature		150	$^{\circ}\text{C}$

Note 1: in fail safe mode, the device acts as a short circuit.

Repetitive peak pulse currenttr: rise time (μs)tp: pulse duration time (μs)ex: Pulse waveform 10/1000 μs tr = 10 μs tp = 1000 μs **ELECTRICAL PARAMETERS** ($T_{amb} = 25^{\circ}\text{C}$)

Type	$I_{RM} @ V_{RM}$ max.		$I_R @ V_R$ max. Note 1		Dynamic V_{BO} max. Note 2	Static $V_{BO} @ I_{BO}$ max. Note 3		I_H min. Note 4	C typ. Note 5	C typ. Note 6
	μA	V	μA	V	V	V	mA	mA	pF	pF
SMP100MC-65*	2	55	50	65	85	80	800	150	30	60
SMP100MC-90*		81		90	115	115		150	30	55
SMP100MC-120*		108		120	155	150		150	25	50
SMP100MC-140*		120		140	180	175		150	20	40
SMP100MC-160*		144		160	205	200		150	20	40
SMP100MC-200*		170		200	255	250		150	20	40
SMP100MC-230*		200		230	295	285		150	20	40
SMP100MC-270		230		270	345	335		150	20	40

Note 1: I_R measured at V_R guarantee $V_{BR} \min \geq V_R$ **Note 2:** See functional test circuit 1**Note 3:** See test circuit 2**Note 4:** See functional holding current test circuit 3**Note 5:** $V_R = 50\text{V}$ bias, $V_{RMS} = 1\text{V}$, $F = 1\text{MHz}$ **Note 6:** $V_R = 2\text{V}$ bias, $V_{RMS} = 1\text{V}$, $F = 1\text{MHz}$

* in development

Fig. 1: On-state voltage versus on-state current (typical values)

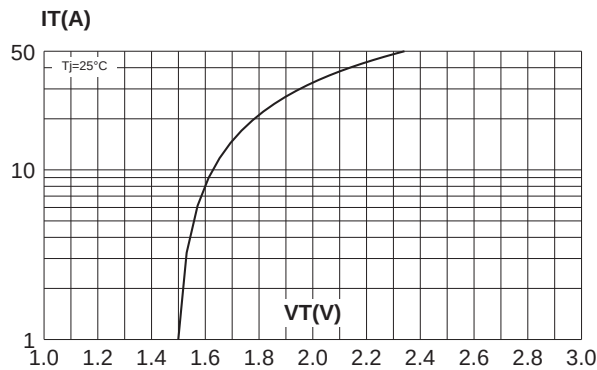


Fig. 2: Relative variation of holding current versus junction temperature .

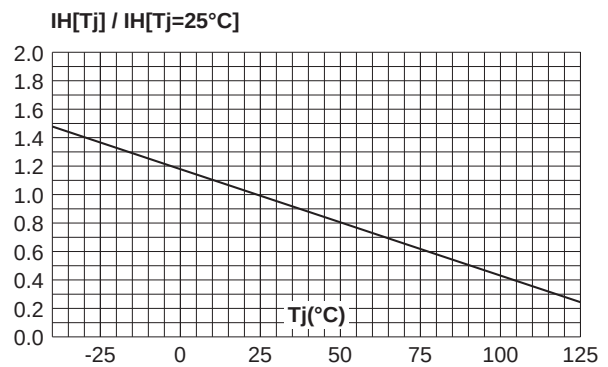


Fig. 3: Relative variation of breakover voltage versus junction temperature.

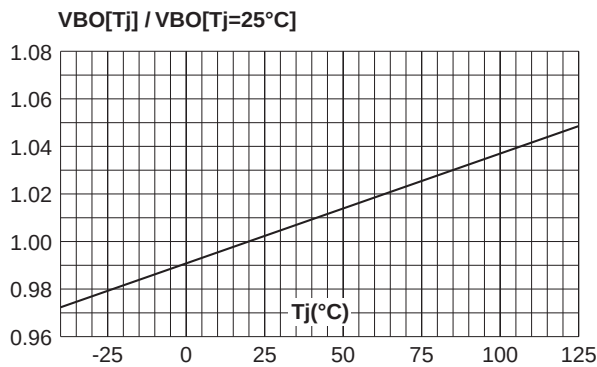


Fig. 4: Relative variation of leakage current versus junction temperature (typical values).

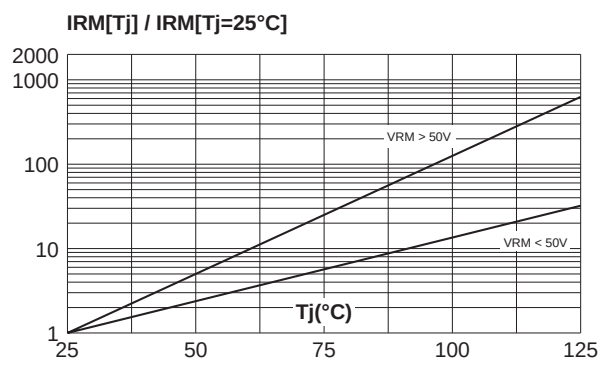


Fig. 5: Variation of thermal impedance junction to ambient versus pulse duration (Printed circuit board FR4, SCu=35μm, recommended pad layout).

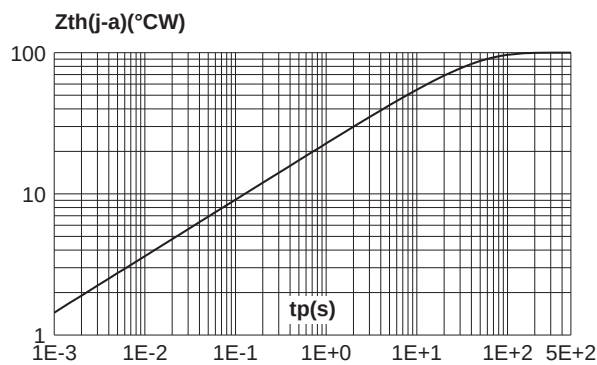
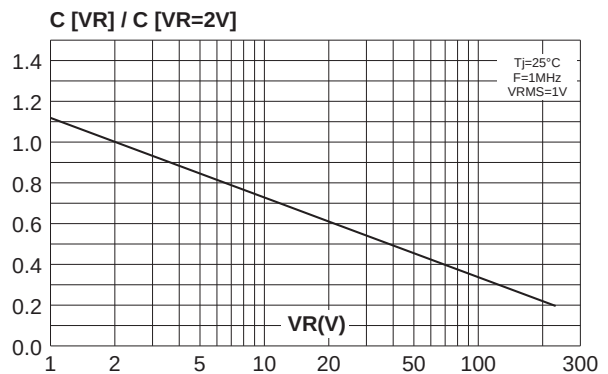
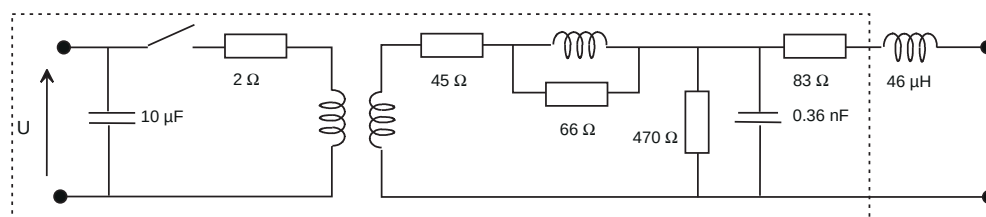
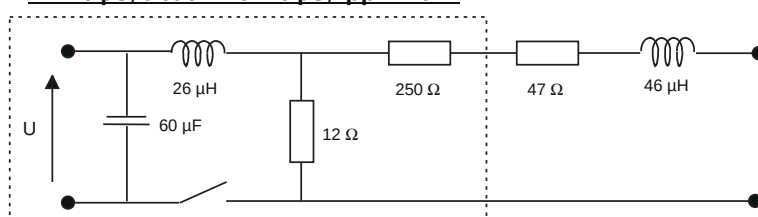


Fig. 6: Relative variation of junction capacitance versus reverse voltage applied (typical values).

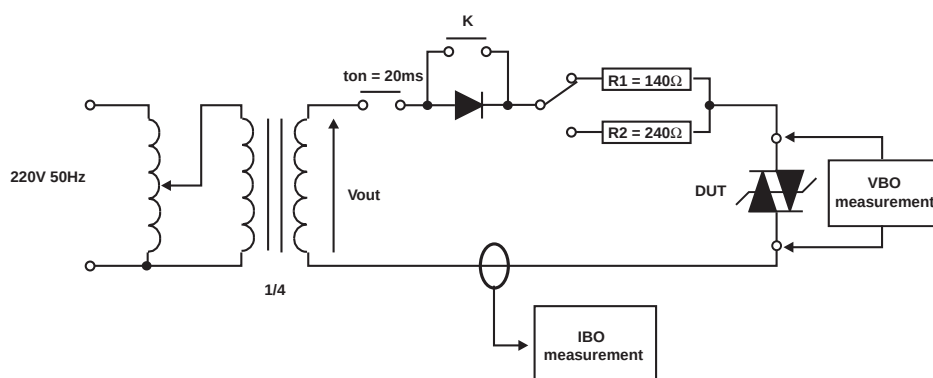


TEST CIRCUIT 1 FOR DYNAMIC I_{B0} AND V_{B0} PARAMETERS**100 V / μ s, $di/dt < 10$ A / μ s, $I_{pp} = 100$ A**

KeyTek 'System 2' generator with PN246I module

1 kV / μ s, $di/dt < 10$ A / μ s, $I_{pp} = 10$ A

KeyTek 'System 2' generator with PN246I module

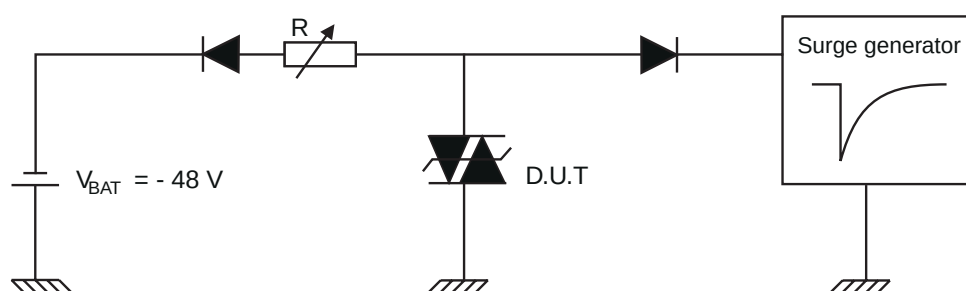
TEST CIRCUIT 2 FOR I_{BO} and V_{BO} parameters :**TEST PROCEDURE :**

Pulse test duration ($t_p = 20\text{ms}$):

- For Bidirectional devices = Switch K is closed
- For Unidirectional devices = Switch K is open.

V_{OUT} Selection

- Device with $V_{BO} < 200\text{ Volt}$
 - $V_{OUT} = 250\text{ V}_{RMS}$, $R_1 = 140\ \Omega$.
- Device with $V_{BO} \geq 200\text{ Volt}$
 - $V_{OUT} = 480\text{ V}_{RMS}$, $R_2 = 240\ \Omega$.

TEST CIRCUIT 3 FOR I_H PARAMETER

This is a GO-NO GO test which allows to confirm the holding current (I_H) level in a functional test circuit.

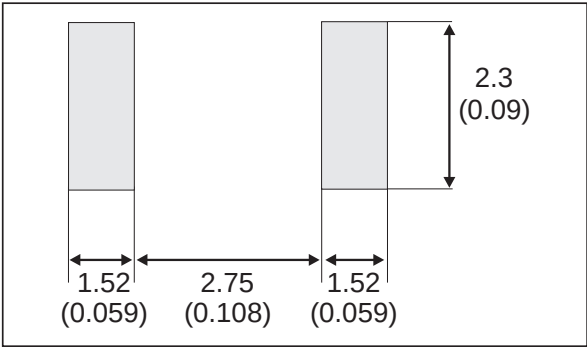
TEST PROCEDURE :

- Adjust the current level at the I_H value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current : $I_{pp} = 10\text{A}$, $10/1000\ \mu\text{s}$.
- The D.U.T. will come back to the off-state within 50 ms max.

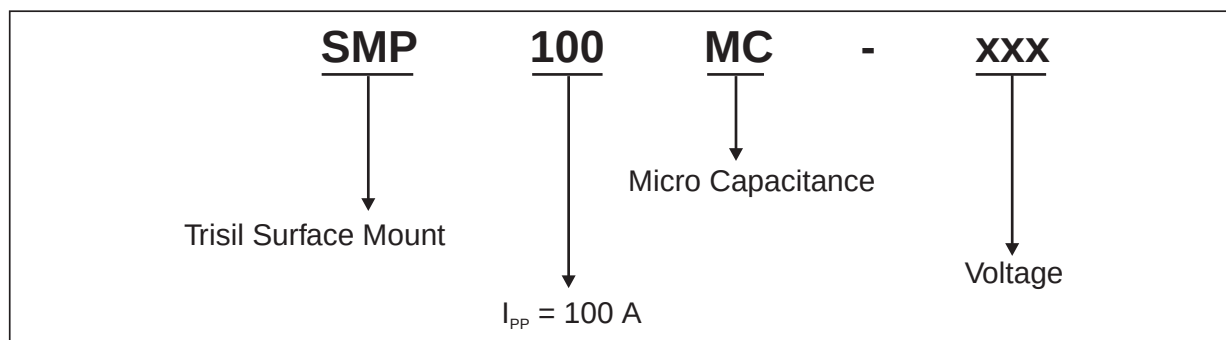
PACKAGE MECHANICAL DATA
SMB (Plastic)

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.41	0.006	0.016
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.60	0.030	0.063

FOOT PRINT in millimeters (inches)



ORDER CODE



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
SMP100MC-65	ML06	SMB	0.11g	2500	Tape & Reel
SMP100MC-90	ML09				
SMP100MC-120	ML12				
SMP100MC-140	ML14				
SMP100MC-160	ML16				
SMP100MC-200	ML20				
SMP100MC-230	ML23				
SMP100MC-270	ML27				

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